

1. General description

Dual Silicon Carbide Schottky diodes in a TO3PF plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- Insulated package rated at 2500V RMS

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

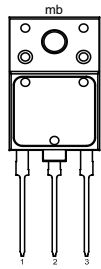
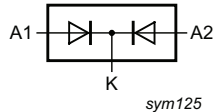
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		650			V
$I_{O(AV)}$	average forward current	$\delta = 0.5$; square-wave pulse; $T_h \leq 51$ °C; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3	20			A
T_j	junction temperature		175			°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10$ A; $T_j = 25$ °C; per diode; Fig. 5	-	1.5	1.7	V
		$I_F = 10$ A; $T_j = 150$ °C; per diode; Fig. 5	-	1.8	2.2	V
Dynamic characteristics						
Q_r	recovered charge	$I_F = 10$ A; $di_F/dt = 500$ A/ μ s; $V_R = 400$ V; $T_j = 25$ °C; per diode; Fig. 7	-	14	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		
3	A2	anode		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D20650CJ	TO3PF	WNSC2D20650CJQ	Tube	30	SOT1293	16-Mar-2006

7. Marking

Table 4. Marking codes

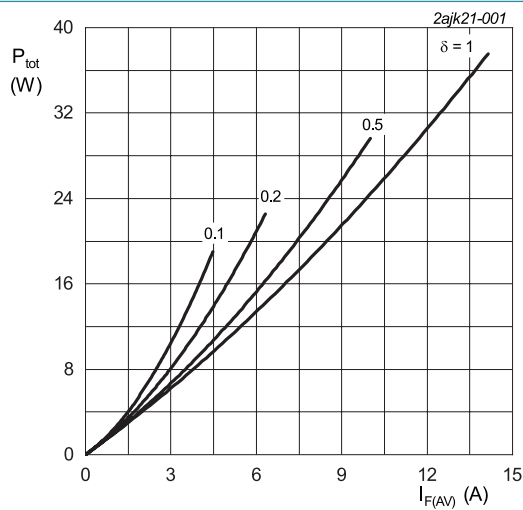
Type number	Marking codes
WNSC2D20650CJ	WNSC2D 20650CJ

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
$I_{O(AV)}$	average forward current	$\delta = 0.5$; square-wave pulse; $T_h \leq 51^\circ\text{C}$; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3	20	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_h \leq 89^\circ\text{C}$; square-wave pulse; per diode	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse; per diode	50	A
		$t_p = 10\ \mu\text{s}$; $T_{j(\text{init})} = 25^\circ\text{C}$; square-wave pulse; per diode	450	A
I^2t	I^2t for fusing	sine-wave pulse; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 10\ \text{ms}$	12.5	A^2s
T_{stg}	storage temperature		-55 to 175	$^\circ\text{C}$
T_j	junction temperature		175	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.916\ \text{V}; R_s = 0.0523\ \Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

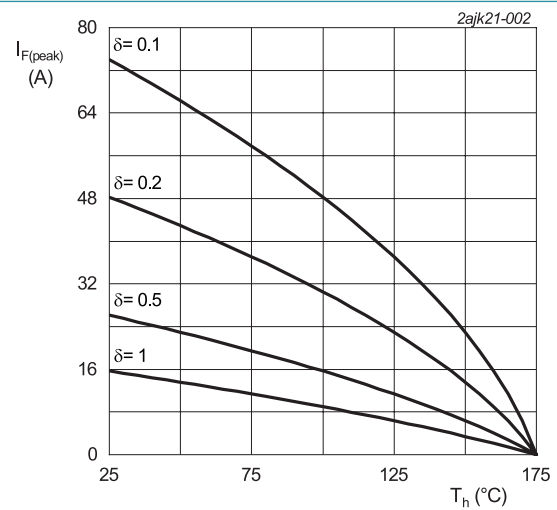


Fig. 2. Current derating as a function of heatsink temperature; per diode

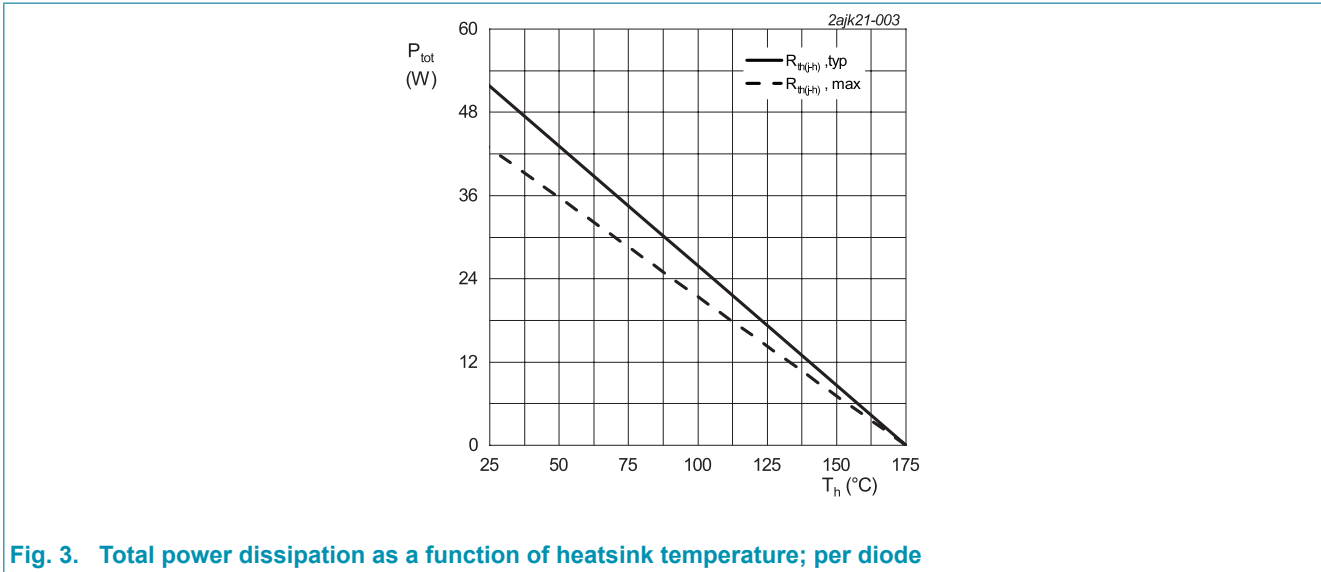


Fig. 3. Total power dissipation as a function of heatsink temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; per diode; Fig. 4	-	-	3.5	K/W
		with heatsink compound; both diodes conducting	-	-	2.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W

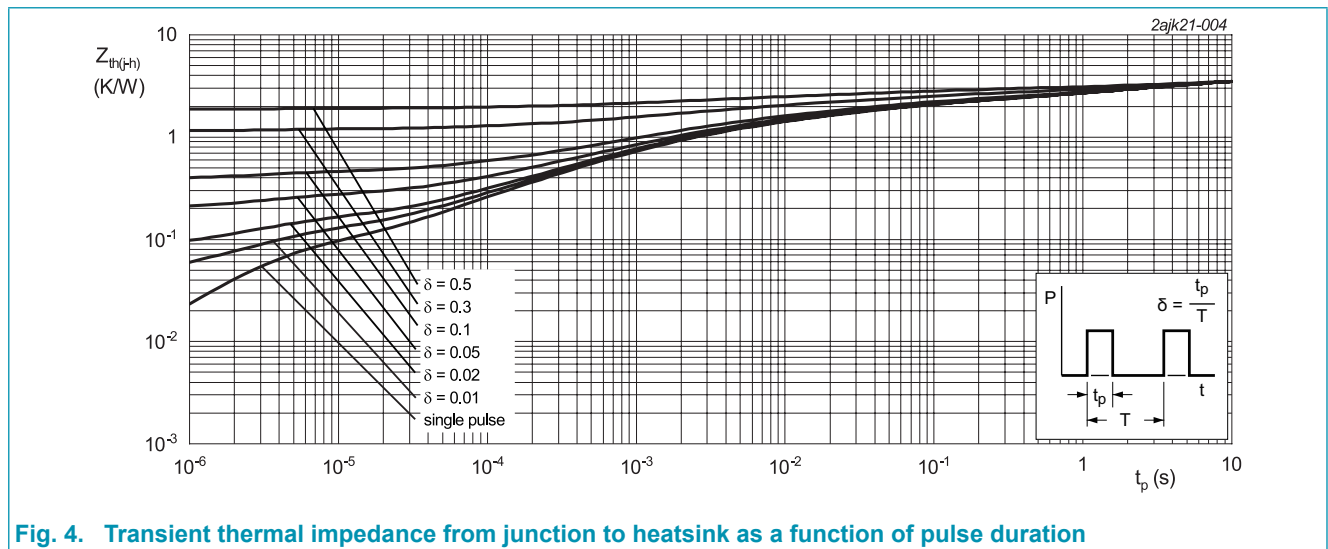


Fig. 4. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

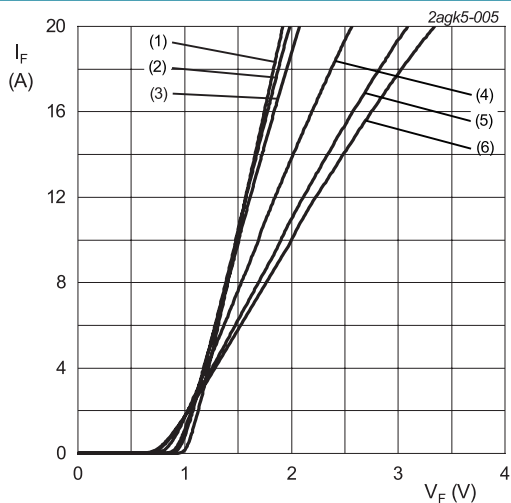
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_F	forward current	$I_F = 10 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 5	-	1.5	1.7	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ per diode; Fig. 5	-	1.8	2.2	V
		$I_F = 10 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ per diode; Fig. 5	-	2	2.3	V
I_R	reverse current	$V_R = 650 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	0.5	50	μA
		$V_R = 650 \text{ V}; T_j = 175 \text{ }^\circ\text{C};$ per diode; Fig. 6	-	25	250	μA
Dynamic characteristics						
Q_r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ per diode; Fig. 7	-	14	-	nC
C_d	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	310	-	pF
		$f = 1 \text{ MHz}; V_R = 300 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	36	-	pF
		$f = 1 \text{ MHz}; V_R = 600 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	32	-	pF
E_{as}	non-repetitive avalanche energy	$I_R = 5.5 \text{ A}; L = 5 \text{ mH}; T_{j(\text{init})} = 25 \text{ }^\circ\text{C};$ per diode	75	-	-	mJ



$V_o = 1.916 \text{ V}; R_s = 0.0523 \text{ } \Omega$
 (1) $T_j = -55 \text{ }^\circ\text{C};$ typical values
 (2) $T_j = 0 \text{ }^\circ\text{C};$ typical values
 (3) $T_j = 25 \text{ }^\circ\text{C};$ typical values
 (4) $T_j = 100 \text{ }^\circ\text{C};$ typical values
 (5) $T_j = 150 \text{ }^\circ\text{C};$ typical values
 (6) $T_j = 175 \text{ }^\circ\text{C};$ typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

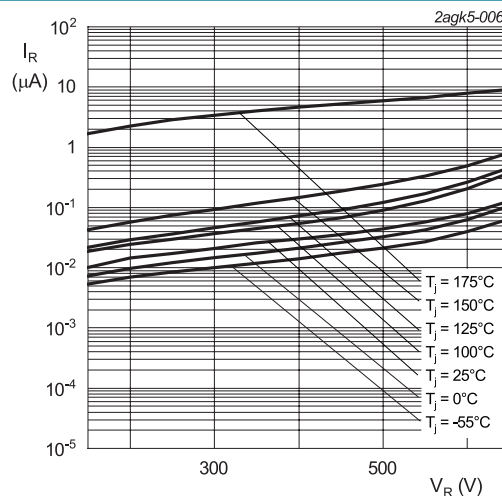


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

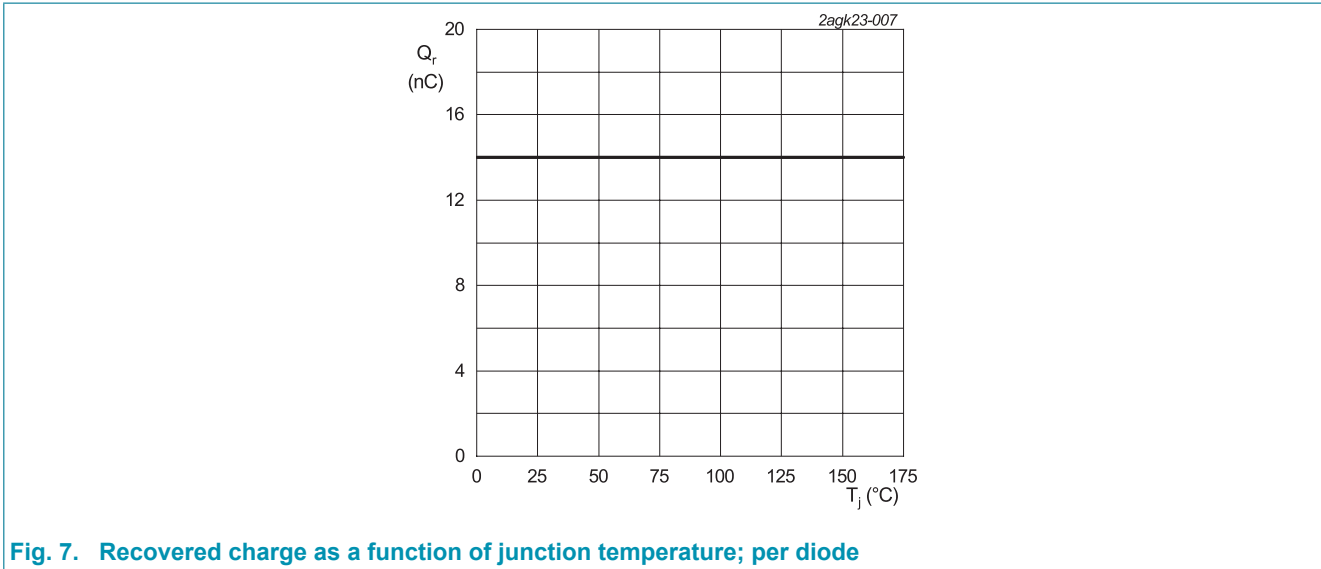
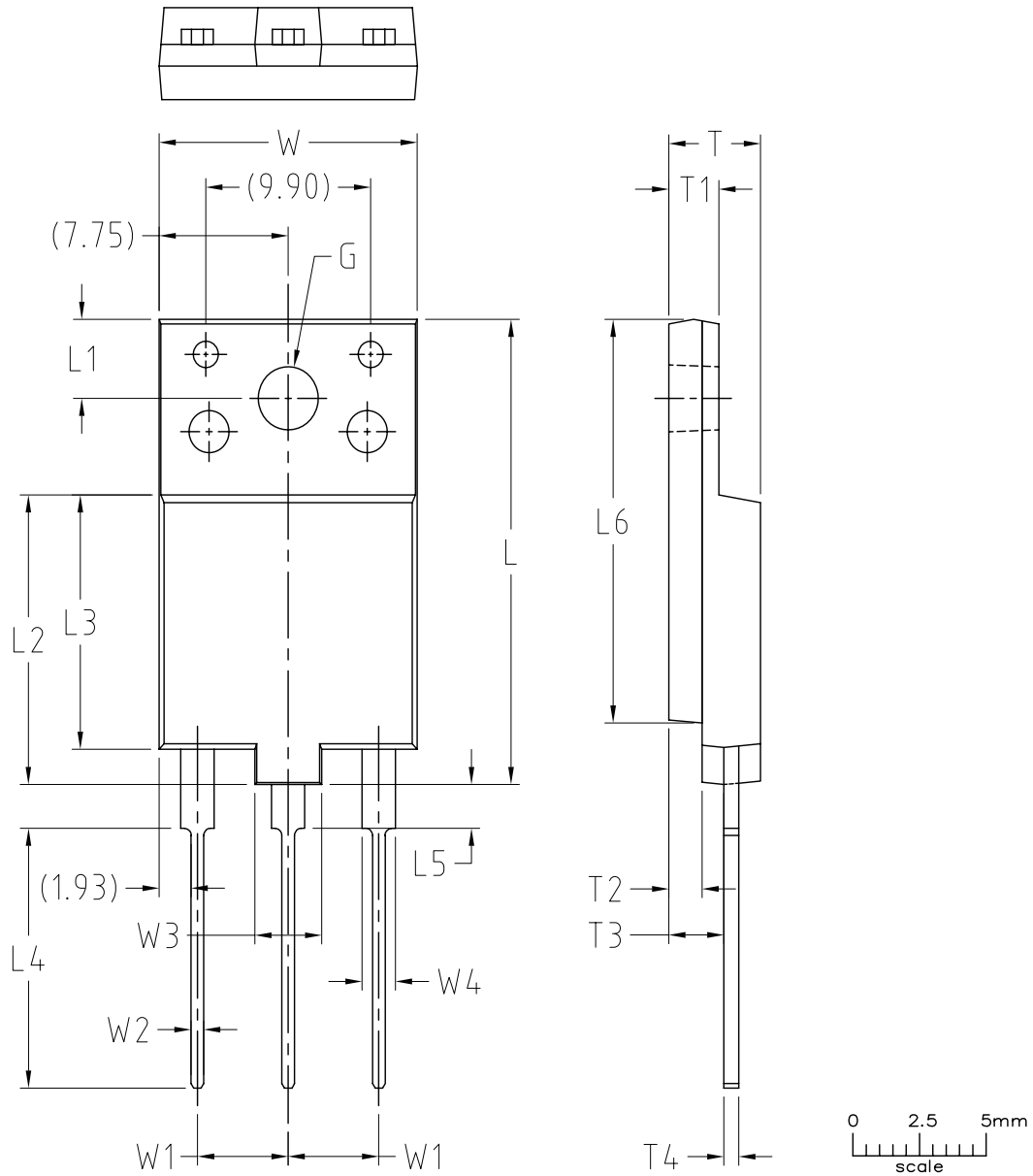


Fig. 7. Recovered charge as a function of junction temperature; per diode

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack' TO3PF



Remark : (X) the dimension X in brackets is for reference

UNIT	W	W1	W2	W3	W4	L	L1	L2	L3	L4	L5	L6	T	T1	T2	T3	T4	G(φ)
mm	15.7	5.75	0.95	4.20	2.20	26.7	4.6	16.7	14.7	15.0	2.7	23.2	5.7	3.2	2.2	3.5	1.1	3.8
	15.3	5.15	0.65	3.80	1.80	26.3	4.4	16.3	14.3	14.6	2.3	22.8	5.3	2.8	1.8	3.1	0.8	3.4

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
		TO-3PF				

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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